

Silicon NPN Power Transistors

2SD1175

DESCRIPTION

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- With TO-3 package
- Built-in damper diode
- High voltage ,high power dissipation
- Wide area of safe operation

APPLICATIONS

- Line-operated horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

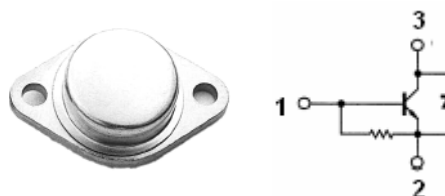


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		5	A
P_T	Total power dissipation	$T_C = 25\square$	100	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-65~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=500mA; I_C=0;$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4.0 A; I_B=0.8 A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4.0 A; I_B=0.8 A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=750V; I_E=0$			50	μA
		$V_{CB}=1500V; I_E=0$			1.0	mA
h_{FE-1}	DC current gain	$I_C=1A; V_{CE}=5V$	10		30	
h_{FE-2}	DC current gain	$I_C=4A; V_{CE}=10V$	5			
V_F	Diode forward voltage	$I_F=4A$			2.5	V

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